

In the claims

Cancel claim 13 without prejudice.

1. (Amended) A method of improving the uniformity of etching of a film having a plurality of solder bumps on an article, the method comprising the steps of

immersing the article containing the film having a plurality of solder bumps into a tank of etchant;

rotating the article while in the etchant for an amount of time so as to cause improved uniformity of etching of the film across the entire article compared to etching without rotating the article; and

removing the article from the tank of etchant.

3. (Amended) The method of claim 1 wherein the step of sequentially rotating comprises rotating the article an amount but less than a complete rotation, etching the article an amount of time, and repeating the steps of rotating and etching for an amount of time.

4. (Amended) The method of claim 1 wherein the step of rotating comprises continuously

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rotating the article an amount of time.

8. (Amended) A method of improving the uniformity of etching of a film having a plurality of solder bumps on a semiconductor wafer, the method comprising the steps of:

immersing the semiconductor wafer containing the film having a plurality of solder bumps into a tank of etchant;

rotating the semiconductor wafer while in the etchant for an amount of time; and

removing the semiconductor wafer from the tank of etchant.

10. (Amended) The method of claim 8 wherein the step of sequentially rotating comprises rotating the semiconductor wafer an amount but less than a complete rotation, etching the semiconductor wafer an amount of time, and repeating the steps of rotating and etching for an amount of time

11. (Amended) The method of claim 8 wherein the step of rotating comprises continuously rotating the semiconductor wafer an amount of time